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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET



Marking code: 8B

PRODUCT SUMMARY					
V _{DS} (V)	60				
$R_{DS(on)}$ (Ω) at $V_{GS} = 1.5 \text{ V}$	1.41				
I _D (A)	0.44				
Configuration	Single				
Package	SC-70				

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q tested
- Typical ESD protection: 800 V
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





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N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	60	V	
Gate-source voltage		V_{GS}	± 8	V	
Continuous drain current ^a	T _C = 25 °C	I _D	0.44	٨	
	T _C = 125 °C		0.25		
Continuous source current (diode conduction) ^a		I _S	0.54	A	
Pulsed drain current ^b		I _{DM}	1.7		
Maximum power dissipation ^b	T _C = 25 °C	- P _D	0.43	W	
	T _C = 125 °C		0.14	VV	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient F	PCB mount c	R_{thJA}	460	°C/W
Junction-to-foot (drain)		R_{thJF}	350	C/VV

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V_{DS}	V _{GS} = 0, I _D = 250 μA		60	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		0.6	1	V	
Cota como locloro		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 3 \text{ V}$		-	-	± 100	nA	
Gate-source leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$		-	100		
		V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	1	
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	- μA -	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	150		
On-state drain current ^a	I _{D(on)}	V _{GS} = 1.5 V	$V_{DS} \ge 5 V$	0.5	-	-	Α	
Drain-source on-state resistance ^a		V _{GS} = 1.5 V	I _D = 2 A	-	0.8	1.41		
	R _{DS(on)}	V _{GS} = 1.5 V	I _D = 1.2 A, T _J = 125 °C	-	-	2.4	Ω	
		V _{GS} = 1.5 V	I _D = 1.2 A, T _J = 175 °C	-	-	3.1		
Forward transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 1 A		-	5.5	-	S	
Dynamic ^b								
Input capacitance	C _{iss}			=.	110	140		
Output capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	=	19	24	pF	
Reverse transfer capacitance	C _{rss}			-	12	15		
Total gate charge ^c	Q_g			=.	2.7	4.1	nC	
Gate-source charge ^c	Q _{gs}	$V_{GS} = 4.5 \text{ V}$	$V_{DS} = 30 \text{ V}, I_D = 2.8 \text{ A}$	=	0.25	-		
Gate-drain charge ^c	Q _{gd}			-	0.35	-		
Gate resistance	R_g	f = 1 MHz		5.8	9	15.5	Ω	
Turn-on delay time ^c	t _{d(on)}			-	12	18		
Rise time ^c	t _r	$V_{DD} = 30 \text{ V}, R_L = 30 \Omega$ $I_D \cong 1 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		-	21	32	ns	
Turn-off delay time ^c	t _{d(off)}			-	8	12		
Fall time ^c	t _f			-	7	11		
Source-Drain Diode Ratings and Char	acteristics ^b							
Pulsed current ^a	I _{SM}				-	1.6	Α	
Forward voltage	V_{SD}	$I_F = 0.8 \text{ A}, V_{GS} = 0$		_	0.8	1.2	V	

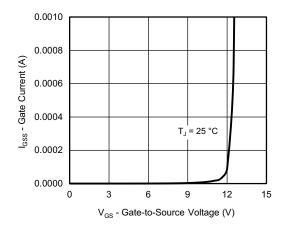
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature

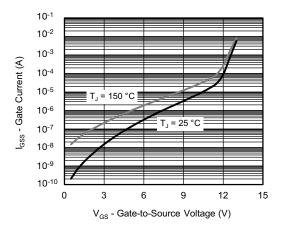
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



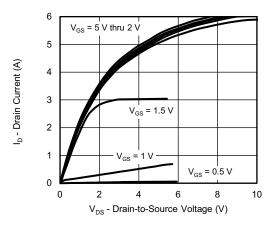
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



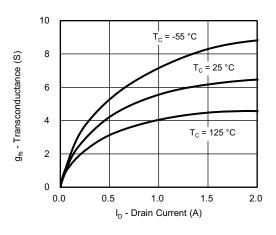
Gate Current vs. Gate-Source Voltage



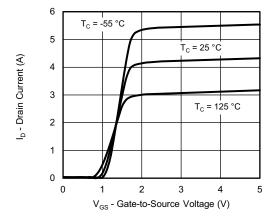
Gate Current vs. Gate-Source Voltage



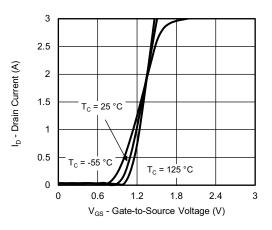
Output Characteristics



Transconductance



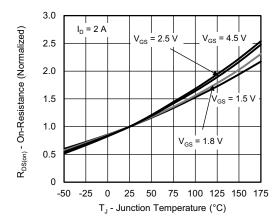
Transfer Characteristics



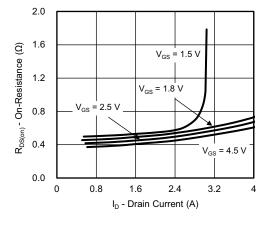
Transfer Characteristics



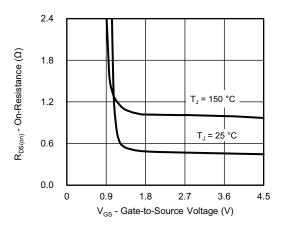
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



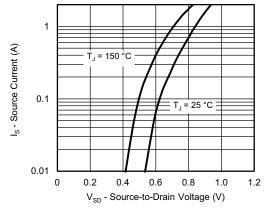
On-Resistance vs. Junction Temperature



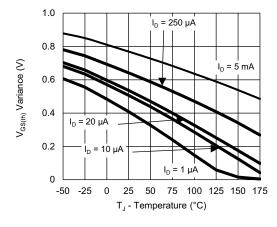
On-Resistance vs. Drain Current



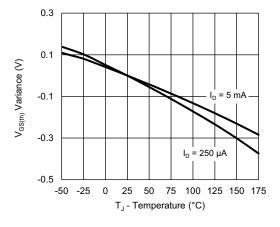
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



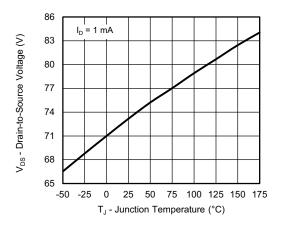
Threshold Voltage



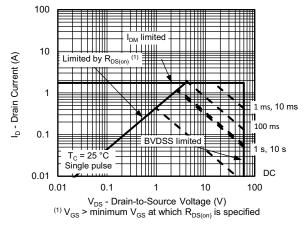
Threshold Voltage



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



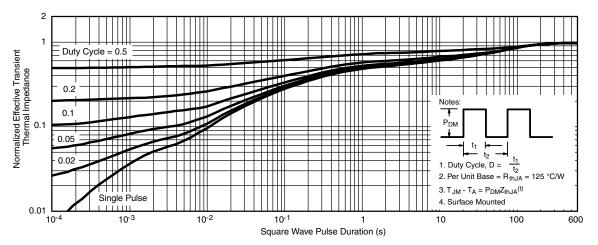
Drain Source Breakdown vs. Junction Temperature



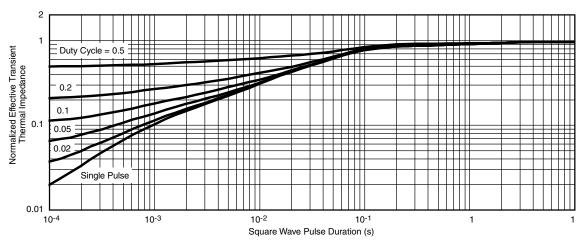
Safe Operating Area



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

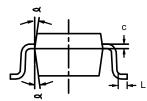
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SC-70: 6-LEADS



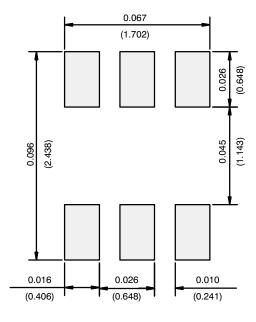


	MILLIMETERS			INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.90	-	1.10	0.035	-	0.043
A ₁	_	-	0.10	_	_	0.004
A ₂	0.80	-	1.00	0.031	_	0.039
b	0.15	-	0.30	0.006	_	0.012
С	0.10	-	0.25	0.004	-	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
Е	1.80	2.10	2.40	0.071	0.083	0.094
E ₁	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65BSC			0.026BSC		
e ₁	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
۵	7°Nom			7°Nom		
ECN: S-03946—Rev. B, 09-Jul-01						

DWG: 5550



RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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